

SEMiX404GB12E4s



Trench IGBT Modules

SEMiX404GB12E4s

Features

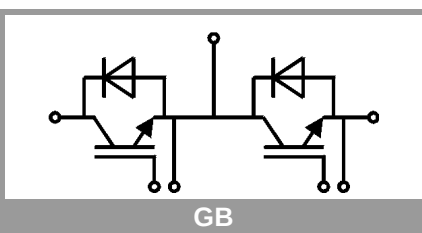
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability
- UL recognized, file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic Welding

Remarks

- Case temperature limited to $T_C=125^\circ\text{C}$ max.
- Product reliability results are valid for $T_J=150^\circ\text{C}$
- For short circuit: Soft R_{Goff} recommended $R_{Goff} > 25$
- Dynamic values apply to the following combination of resistors:
 $R_{Gon,main} = 1,0 \Omega$
 $R_{Goff,main} = 1,0 \Omega$
 $R_{G,X} = 2,2 \Omega$
 $R_{E,X} = 0,5 \Omega$



Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
IGBT				
V _{CES}			1200	V
I _C	T _j = 175 °C	T _c = 25 °C	618	A
		T _c = 80 °C	475	A
I _{Cnom}			400	A
I _{CRM}	I _{CRM} = 3xI _{Cnom}		1200	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 800 V V _{GE} ≤ 20 V V _{CES} ≤ 1200 V	T _j = 150 °C	10	µs
T _j			-40 ... 175	°C
Inverse diode				
I _F	T _j = 175 °C	T _c = 25 °C	440	A
		T _c = 80 °C	329	A
I _{Fnom}			400	A
I _{FRM}	I _{FRM} = 3xI _{Fnom}		1200	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 25 °C		1980	A
T _j			-40 ... 175	°C
Module				
I _{t(RMS)}			600	A
T _{stg}			-40 ... 125	°C
V _{isol}	AC sinus 50Hz, t = 1 min		4000	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
IGBT						
V _{CE(sat)}	I _C = 400 A	T _j = 25 °C		1.8	2.05	V
	V _{GE} = 15 V chipelevel	T _j = 150 °C		2.2	2.4	V
V _{CE0}		T _j = 25 °C		0.8	0.9	V
		T _j = 150 °C		0.7	0.8	V
r _{CE}	V _{GE} = 15 V	T _j = 25 °C		2.5	2.9	mΩ
		T _j = 150 °C		3.8	4.0	mΩ
V _{GE(th)}	V _{GE} =V _{CE} , I _C = 15.2 mA		5	5.8	6.5	V
I _{CES}	V _{GE} = 0 V	T _j = 25 °C		0.12	0.36	mA
	V _{CE} = 1200 V	T _j = 150 °C				mA
C _{ies}	V _{CE} = 25 V	f = 1 MHz		24.6		nF
C _{oes}	V _{GE} = 0 V	f = 1 MHz		1.62		nF
C _{res}		f = 1 MHz		1.38		nF
Q _G	V _{GE} = - 8 V...+ 15 V			2260		nC
R _{Gint}	T _j = 25 °C			1.88		Ω
t _{d(on)}	V _{CC} = 600 V	T _j = 150 °C		296		ns
t _r	I _C = 400 A	T _j = 150 °C		67		ns
E _{on}	R _{G on} = 1.7 Ω	T _j = 150 °C		27		mJ
t _{d(off)}	R _{G off} = 1.7 Ω	T _j = 150 °C		634		ns
t _f	di/dt _{on} = 5800 A/μs	T _j = 150 °C		137		ns
E _{off}	di/dt _{off} = 3700 A/μs	T _j = 150 °C		59.7		mJ
R _{th(I-c)}	per IGBT				0.072	K/W

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SEMiX® 4s

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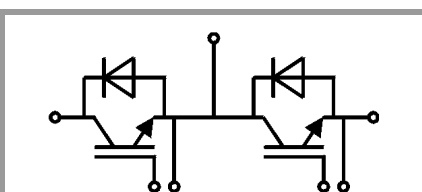
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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
V _F = V _{EC}	I _F = 400 A	T _j = 25 °C		2.2	2.52	V
	V _{GE} = 0 V chip	T _j = 150 °C		2.1	2.5	V
V _{F0}		T _j = 25 °C	1.1	1.3	1.5	V
		T _j = 150 °C	0.7	0.9	1.1	V
r _F		T _j = 25 °C	2.0	2.3	2.5	mΩ
		T _j = 150 °C	2.6	3.1	3.4	mΩ
I _{RRM}	I _F = 400 A	T _j = 150 °C		315		A
Q _{rr}	di/dt _{off} = 4900 A/μs	T _j = 150 °C		63		μC
E _{rr}	V _{GE} = -15 V V _{CC} = 600 V	T _j = 150 °C		26.4		mJ
R _{th(j-c)}	per diode				0.14	K/W
Module						
L _{CE}				22		nH
R _{CC'+EE'}	res., terminal-chip	T _C = 25 °C		0.7		mΩ
		T _C = 125 °C		1		mΩ
R _{th(c-s)}	per module			0.03		K/W
M _s	to heat sink (M5)		3		5	Nm
M _t		to terminals (M6)	2.5		5	Nm
				Nm		
w					400	g
Temperatur Sensor						
R ₁₀₀	T _c =100°C (R ₂₅ =5 kΩ)			493 ± 5%		Ω
B _{100/125}	R _(T) =R ₁₀₀ exp[B _{100/125} (1/T-1/T ₁₀₀)]; T[K];			3550 ±2%		K



GB

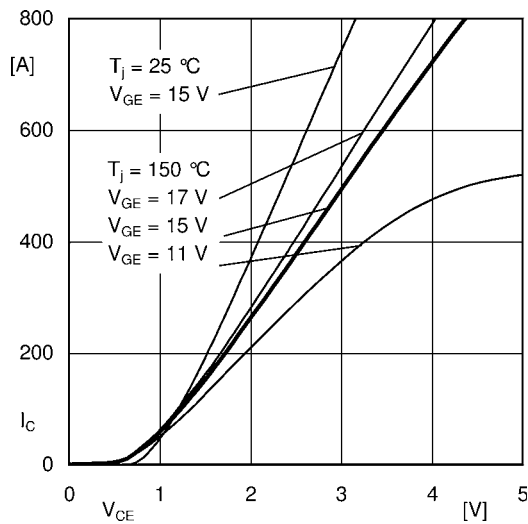


Fig. 1: Typ. output characteristic, inclusive $R_{CC'} + EE'$

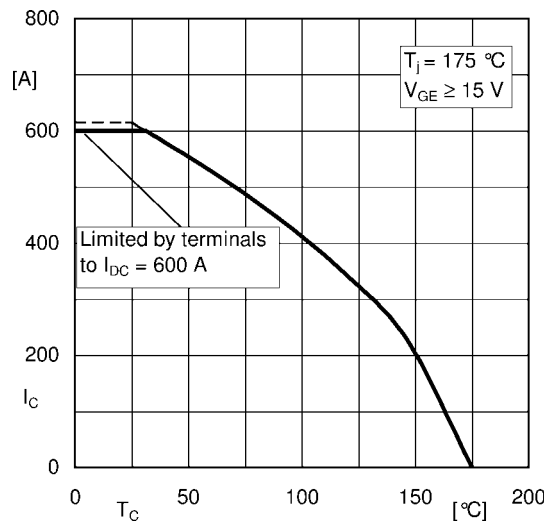


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

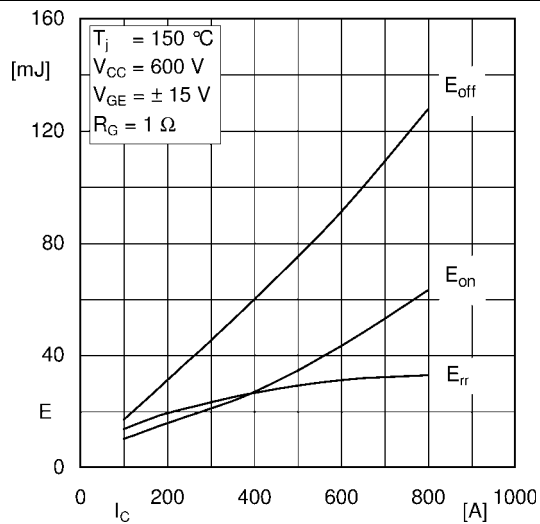


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

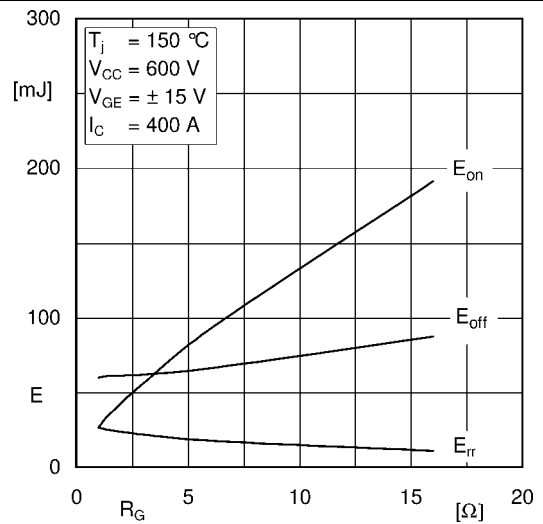


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

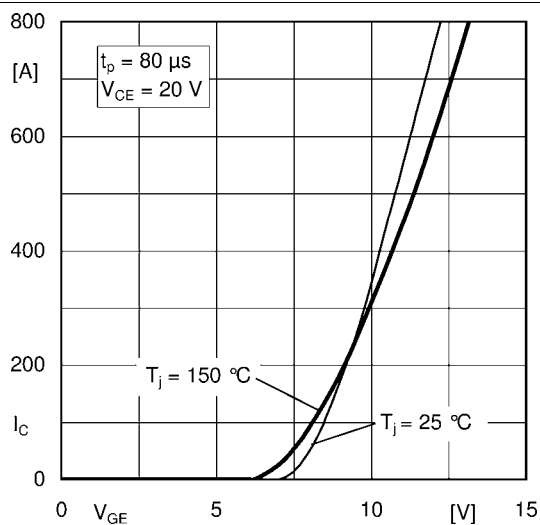


Fig. 5: Typ. transfer characteristic

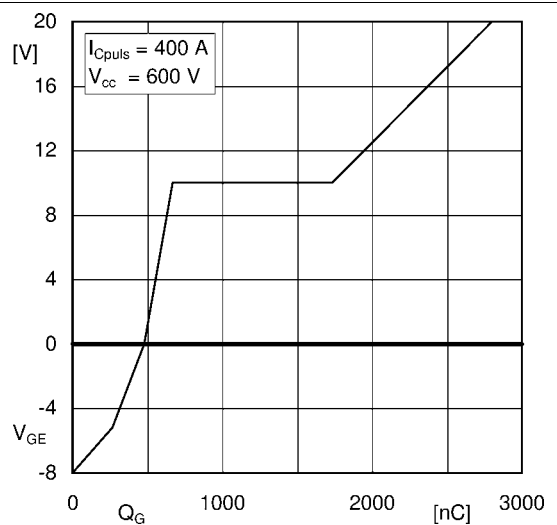
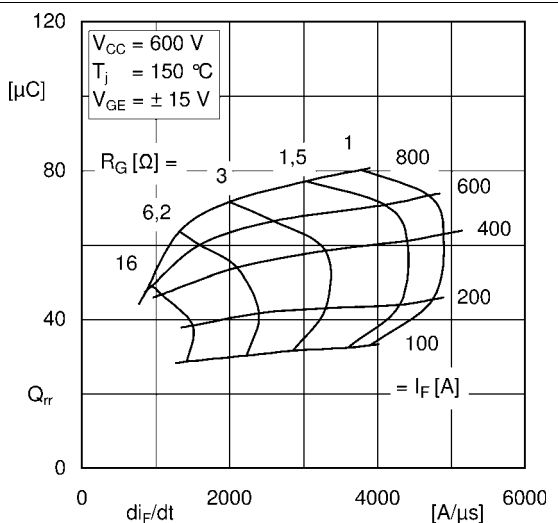
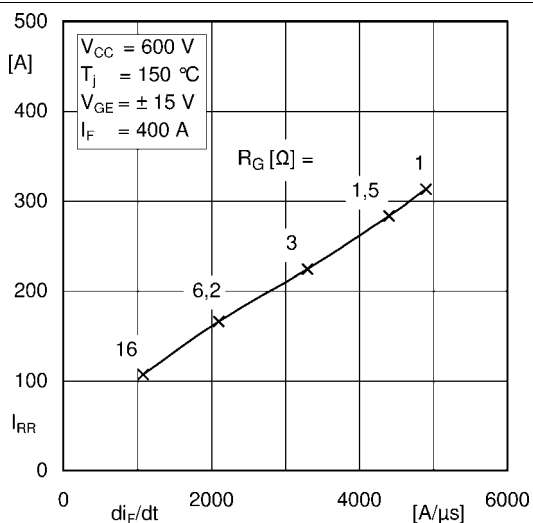
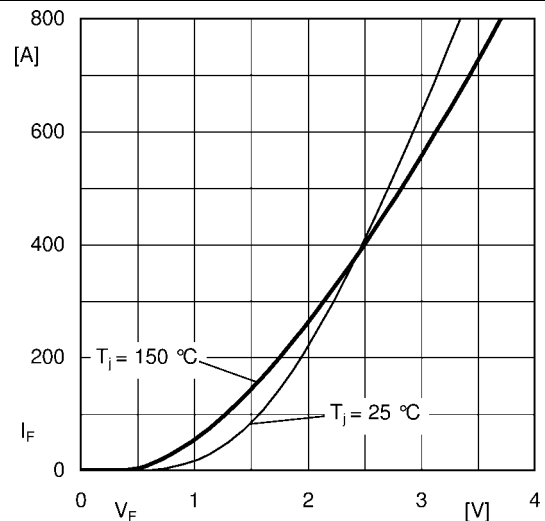
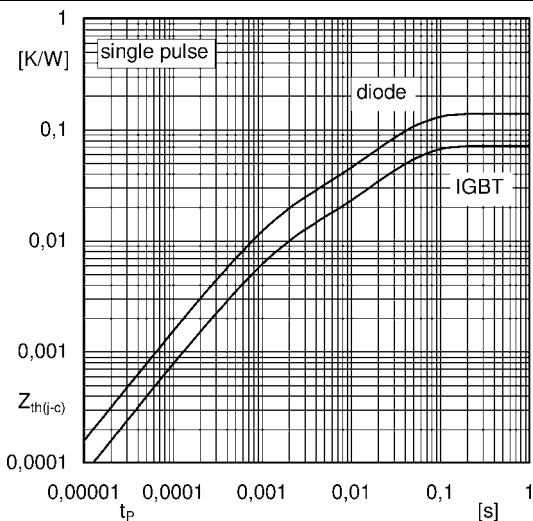
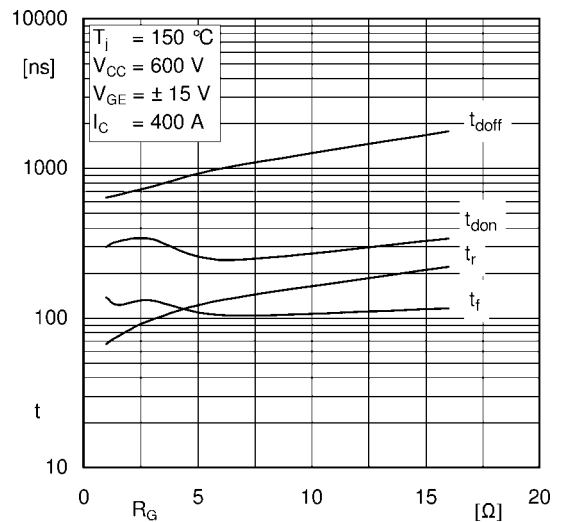
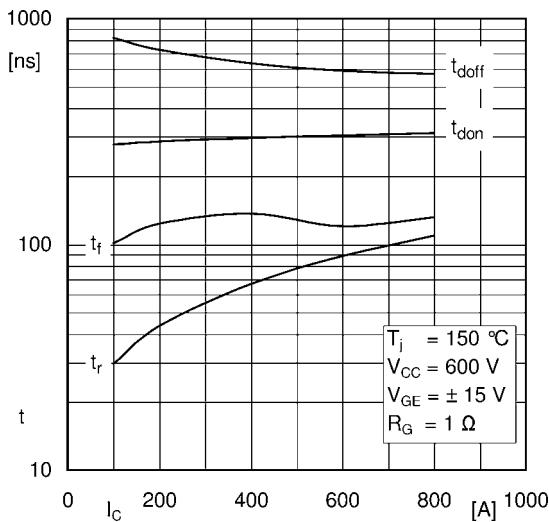
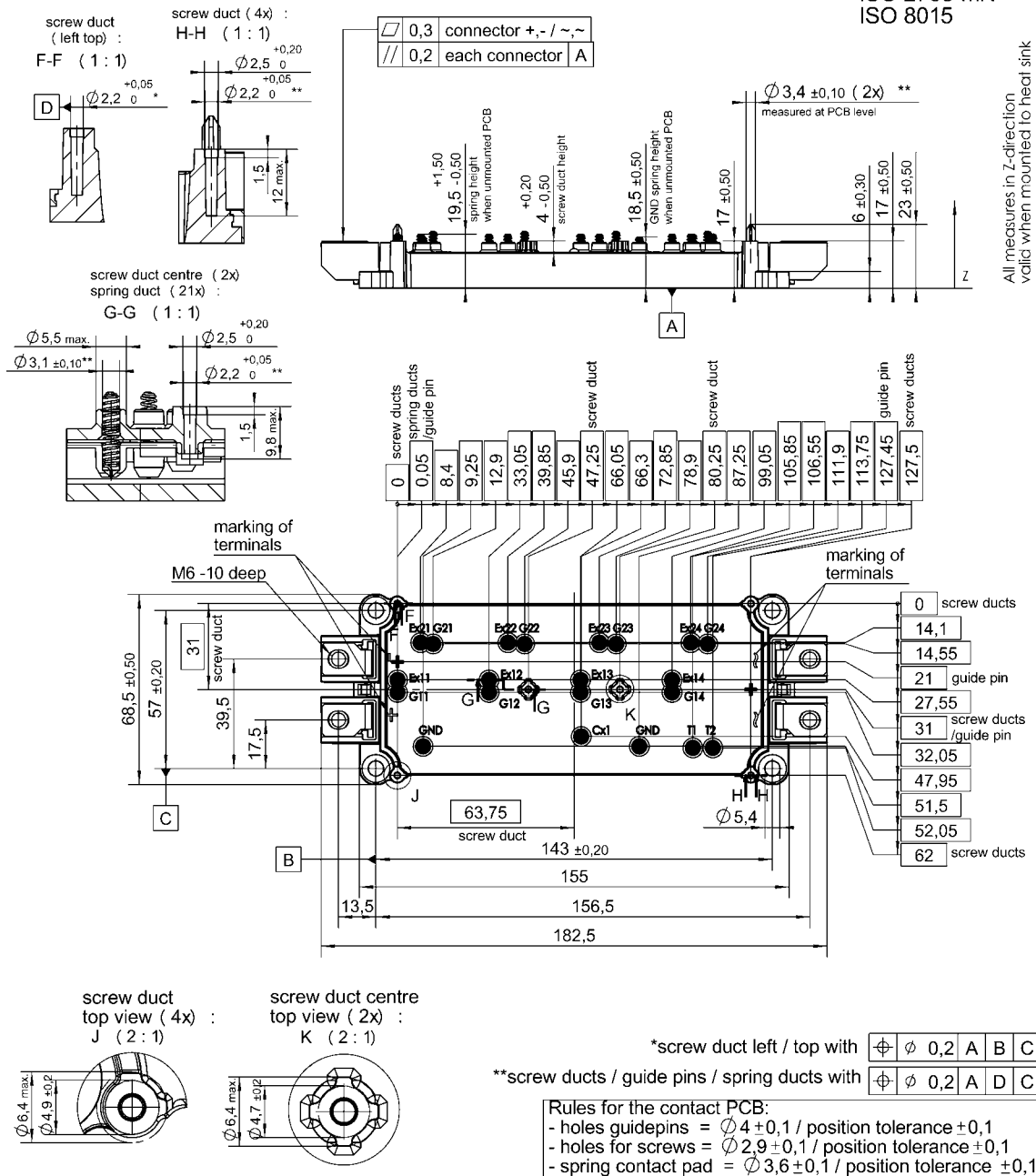


Fig. 6: Typ. gate charge characteristic



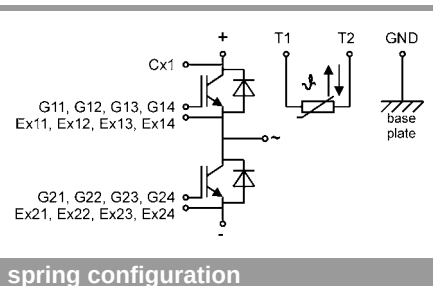
Case: SEMiX 4s

general tolerance:
ISO 2768-mK
ISO 8015



All measures in Z-direction valid when mounted to head sink

SEMiX 4s



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.